

### Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

1. (currently amended) A method of forming a contact in a semiconductor device, comprising:
  - forming an insulating layer on a semiconductor substrate;
  - forming a contact hole in the insulating layer by selectively etching a portion of the insulating layer;
  - forming a barrier metal layer having a uniform thickness on the insulating layer and a surface of the contact hole;
  - forming a wetting layer of an oxidation-resistive metal material of tungsten on the barrier metal layer by a chemical vapor deposition (CVD) process or an atomic layer deposition (ALD) process, wherein a metal of the wetting layer is different than a metal of the barrier layer; and
  - forming a metal layer on the wetting layer so as to fill the contact hole.
2. (cancelled)
3. (currently amended) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the wetting layer is formed by a ~~chemical vapor deposition (CVD) process or an atomic layer deposition (ALD) process.~~
4. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the wetting layer is formed at a temperature of about 350°C to about 550°C.
5. (original) The method of forming a contact in a semiconductor as

claimed in claim 1, wherein the wetting layer is formed to a thickness of about 10Å to about 1000Å.

6. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the wetting layer is formed to such a thickness that sufficient space remains in the contact hole for the metal layer.

7. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the barrier metal layer includes a titanium layer, a titanium nitride layer or a composite layer thereof.

8. (original) The method of forming a contact in a semiconductor as claimed in claim 7, wherein the barrier metal layer is formed by a physical vapor deposition (PVD) process, a chemical vapor deposition (CVD) process, or an atomic layer deposition (ALD) process.

9. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the barrier metal layer is formed to such a thickness that sufficient space remains in the contact hole for the wetting layer and the metal layer.

10. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the metal layer is formed by:

depositing a metal material on the wetting layer to such a thickness that the contact hole is partially filled; and

re-flowing the deposited metal material to completely fill the contact hole.

11. (original) The method of forming a contact in a semiconductor as

claimed in claim 10, wherein the metal material is deposited through a chemical vapor deposition (CVD) process or a physical vapor deposition (PVD) process.

12. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the metal layer is formed by:

depositing a first metal material on the wetting layer by a chemical vapor deposition (CVD) process to such a thickness that the contact hole is partially filled with the first metal material;

depositing a second metal material on the first metal material by a physical vapor deposition (PVD) process; and

re-flowing the first metal material and the second metal material to completely fill the contact hole.

13. (original) The method of forming a contact in a semiconductor as claimed in claim 12, wherein the first metal material is the same as the second metal material.

14. (original) The method of forming a contact in a semiconductor as claimed in claim 1, wherein the metal layer includes aluminum or an aluminum alloy.